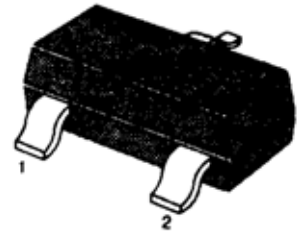


■■ APPLICATION: High Current Applications.

■■ MAXIMUM RATINGS (Ta=25°C)

SOT-323

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CB0}	40	V
Collector-emitter voltage	V _{CEO}	25	V
Emitter-base voltage	V _{EBO}	6	V
Collector current	I _c	1.2	A
Collector Power Dissipation	P _c	300	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	- 55~150	°C



1.Base 2..Emitter 3.Collector

■■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h _{FE}	85		320		V _{CE} = 1 V, I _c = 100 mA
Collector Cut-off Current	I _{CB0}			0.1	μA	V _{CB} = 35 V, I _E =0
Emitter Cut-off Current	I _{EBO}			0.1	μA	V _{EB} =6 V, I _c =0
Collector-Base Breakdown Voltage	BV _{CB0}	40			V	I _c = 0.1 mA, I _E =0
Collector-Emitter Breakdown Voltage	BV _{CEO}	25			V	I _c = 2 mA, I _B =0
Emitter-Base Breakdown Voltage	BV _{EBO}	6			V	I _E = 0.1 mA, I _c =0
Base-Emitter Voltage	V _{BE}			1	V	V _{CE} = 1 V, I _c =10 mA
Collector-Emitter Saturation Voltage	V _{CE(sat)}			0.5	V	I _c = 800 mA, I _B = 80 mA
Base-Emitter Saturation Voltage	V _{BE(sat)}			1.2	V	I _c = 800 mA, I _B = 80 mA
Gain bandwidth product	f _r	100			MHz	I _c =50 mA, V _{CE} = 10 V
Common Base Output Capacitance	C _{ob}		15	30	PF	V _{CB} = 10 V, I _E =0, f=1MHz

■■ h_{FE} Classification And Marking

Print Mark

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Classification

 h_{FE}

160~320